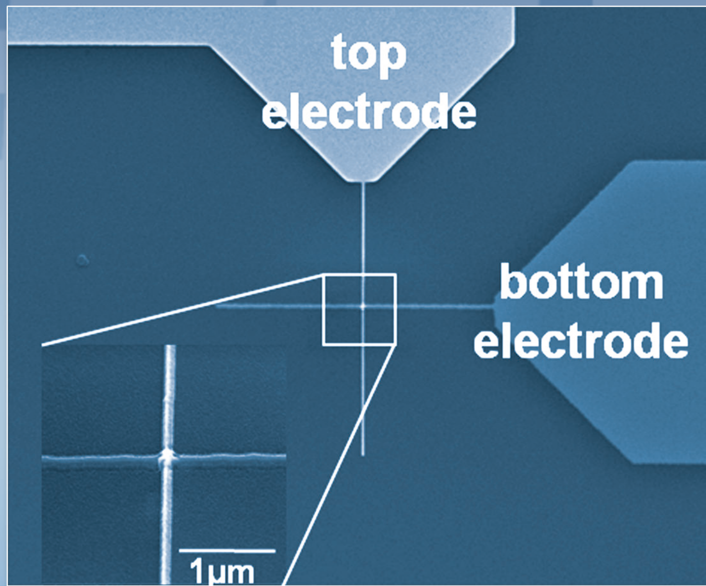

Interaction between Redox-Based Resistive Switching Mechanisms

Christoph Rudolf Hermes

Member of the Helmholtz Association

JÜLICH
FORSCHUNGSZENTRUM

Forschungszentrum Jülich GmbH
Peter Grünberg Institute (PGI)
Electronic Materials (PGI-7)

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